TOSHIBA Bi-CMOS Digital Integrated Circuit Silicon Monolithic

# TD74BC541P,TD74BC541F

Octal Bus Buffer with 3-State Outputs (Non-Inverted)

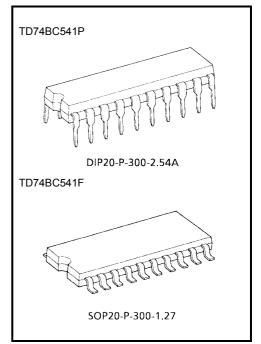
The TD74BC541P/TD74BC541F is a high-speed octal 3-state buffer fabricated with silicon gate Bi-CMOS technology. It achieves the high-speed operation equivalent to the FAST family while maintaining the Bi-CMOS low-power dissipation. The TD74BC541P/F is a non-inverting buffer. It is controlled by two enable inputs ( $\overline{\text{OE}}$ 0,  $\overline{\text{OE}}$ 1). When either  $\overline{\text{OE}}$ 0 and  $\overline{\text{OE}}$ 1 are high, all eight outputs are in the high-impedance state, which facilitates the interface with bus lines.

All inputs are equipped with resistors and diodes to protect against Electro Static Discharge (ESD).

#### **Features**

•	High-speed operation $t_{pd} = 4.8 \text{ ns (typ.)}$
•	Symmetrical output impedance $IOH = -15 \text{ mA (max)}$
	$I_{OL} = 48 \text{ mA (max)}$
•	Low power dissipation $I_{CCD} = 8 \text{ mA (typ.)}$
	$I_{CCZ} = 10 \mu A \text{ (typ.)}$
•	Operating temperature range Ta = $-40$ °C to $85$ °C
•	High ESD protection

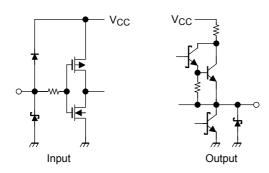
• Pin and function compatible with FAST (74F541)



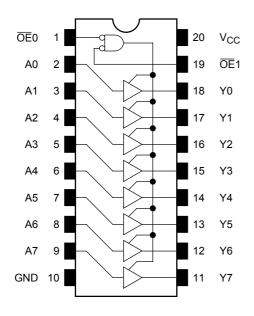
Weight

DIP20-P-300-2.54A: 1.48 g (typ.) SOP20-P-300-1.27: 0.25 g (typ.)

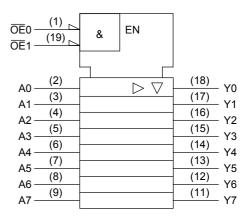
#### Input Protection Circuit and Output Equivalent Circuit



# Pin Assignment (top view)



# **Logic Symbol**



#### **Truth Table**

	Outputs		
ŌĒ0	ŌE1	An	Yn
Н	Х	Х	Z
Х	Н	Х	Z
L	L	Н	Н
L	L	L	L

X: Don't care

Z: High impedance

#### **Absolute Maximum Ratings**

Characteristi	cs	Symbol	Rating	Unit	
Power supply voltage		$V_{CC}$	–0.5 to 7.0	V	
Input voltage		V <sub>IN</sub>	-1.2 to V <sub>CC</sub> + 0.5	V	
Output voltage		Vo	-0.5 to V <sub>CC</sub> + 0.5	V	
Input clamp diode current		I <sub>IK</sub>	±30	mA	
Output clamp diode current		I <sub>OK</sub>	-30	mA	
Output current (output low state)		I <sub>OL</sub>	96	mA	
Power dissipation	BC541P	P <sub>D</sub>	1380 (Note 1)	mW	
i owei dissipation	BC541F		860 (Note 1)	11100	
Storage temperature		T <sub>stg</sub>	-65 to 150	°C	

Note 1:  $Ta = 25^{\circ}C$ 

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# **Recommended Operating Conditions**

Characteristics		Symbol	Min	Тур.	Max	Unit	
Power supply voltage	V <sub>CC</sub>	4.5	5.0	5.5	V		
Input voltage	V <sub>IN</sub>	0		V <sub>CC</sub>	٧		
Output voltage	Vo	0	_	V <sub>CC</sub>	٧		
Output current	High level	I <sub>OH</sub>	_	_	-15	mA	
Output current	Low level	l <sub>OL</sub>	_	_	48	ША	
Operating temperatur	T <sub>opr</sub>	-40	25	85	°C		

#### **Electrical Characteristics**

# DC Characteristics (unless otherwise specified, $V_{CC} = 4.5 \text{ V}$ to 5.5 V, $Ta = -40^{\circ}\text{C}$ to 85°C)

Characteristics		Symbol	Test Condition	V <sub>CC</sub>	Min	Typ. (Note 1)	Max	Unit	
Input voltage	High level	V <sub>IH</sub>	_	_	2.0	_	_	· V	
Input voltage	Low level	V <sub>IL</sub>	_	_	_	_	0.8		
Input clamp voltage		V <sub>IK</sub>	I <sub>IK</sub> = -18 mA	4.5	_	_	-1.2	V	
			$I_{OH} = -3.0 \text{ mA}$	4.5	2.4	3.4	_		
	High level	$V_{OH}$	I <sub>OH</sub> = -3.0 mA	4.75	2.7	3.4	_		
Output voltage			I <sub>OH</sub> = -15 mA	4.5	2.0	_	_	V	
	Low level	V/	I <sub>OL</sub> = 24 mA	4.5	_	_	0.5		
	Low level	$V_{OL}$	I <sub>OL</sub> = 48 mA	4.5	_	_	0.55		
		l <sub>l</sub>	$V_{IN} = V_{CC}$	5.5	_	_	±1.0		
Input current (all input p	oins)	I <sub>IH</sub>	V <sub>IN</sub> = 2.7 V	5.5	_	_	±1.0	μΑ	
	<u>-</u>	I <sub>IL</sub>	V <sub>IN</sub> = 0.5 V or GND	5.5	_	_	±1.0		
2 state OFF lookage ou			V <sub>O</sub> = 2.7 V	5.5	_	_	50	^	
3-state OFF leakage cu	irent -	I <sub>OZL</sub>	$V_{O} = 0.5 \text{ V}$	5.5	_	_	-50	μΑ	
Output short current (Note 2)		I <sub>OS</sub>	$V_O = GND$	5.5	-100	_	-255	mA	
Ic			V <sub>IN</sub> = V <sub>CC</sub> or ground All outputs are low.	5.5	_	20	27	mA	
Quiescent supply curre	nt (total)	I <sub>CCH</sub>	$V_{IN} = V_{CC}$ or ground All outputs are high.	5.5	_	10	50		
		Iccz	V <sub>IN</sub> = V <sub>CC</sub> or ground All outputs are in the high-impedance state.  5.5 —		_	10	50	μА	
Oujescent supply curre	ot (each hit)	Δl <sub>CC1</sub>	One input: $V_{IN} = 0.5 \text{ V}$ Other inputs: $V_{CC}$ or GND	_	—	_	1.5	mA	
Quiescent supply current (each bit)		Δl <sub>CC2</sub>	One input: $V_{IN} = V_{CC} - 2.1 \text{ V}$ Other inputs: $V_{CC}$ or GND		_	_	1.5	IIIA	

Note 1: Typical value is measured at  $V_{CC} = 5.0 \text{ V}$  and  $T_{a} = 25^{\circ}\text{C}$ .

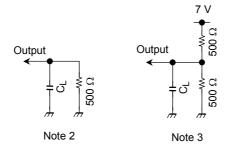
Note 2: Only one output at a time should be shorted. Duration should not exceed one second.

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# AC Characteristics (Input $t_r = t_f = 2.5 \text{ ns}$ )

Characteristics		Symbol	Test Condition	Ta = 25°C V <sub>CC</sub> = 5.0 V			$Ta = -40^{\circ}$ $V_{CC} = 5.0$	Unit	
		Cymbol	reat condition	Min	Тур.	Max	Min	Max	Onit
Propagation delay time	A-Y	t <sub>pLH</sub>	- C <sub>L</sub> = 50 pF	2.0	5.0	6.3	2.0	7.5	ns
Tropagation delay time		t <sub>pHL</sub>		2.0	4.5	5.8	2.0	6.8	
3-state output enable time	ŌĒ-Y	t <sub>pZH</sub>		2.0	8.0	9.5	2.0	11.0	- ns
5-state output enable time		t <sub>pZL</sub>		2.0	6.5	9.5	2.0	11.0	
3-state output disable time	OE -Y	t <sub>pHZ</sub>		2.0	6.0	9.5	2.0	10.0	ns
5-state output disable time		t <sub>pLZ</sub>		2.0	5.0	8.5	2.0	9.5	113
Dynamic supply current		1	f = 1 MHz	_	_ 8	13	_	16	mA
		ICCD	Output open						IIIA

Note 1: When measuring  $t_{pLH}$ ,  $t_{pHL}$ ,  $t_{pZH}$  and  $t_{pHZ}$ , the output pin should be connected as shown in Note 2. When measuring  $t_{pZL}$ , and  $t_{pLZ}$ , the output pin should be connected as shown in Note 3.

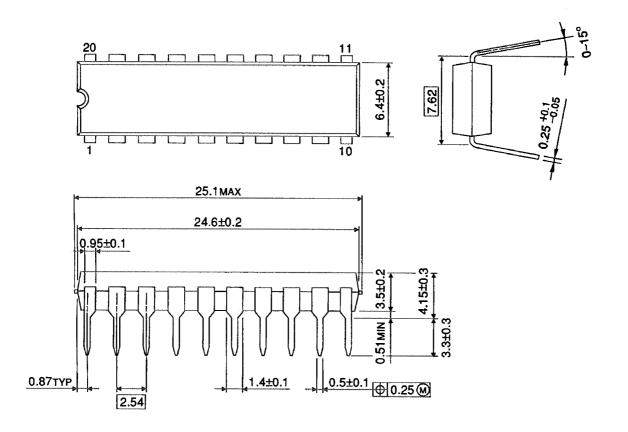


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# **Package Dimensions**

DIP20-P-300-2.54A Unit: mm

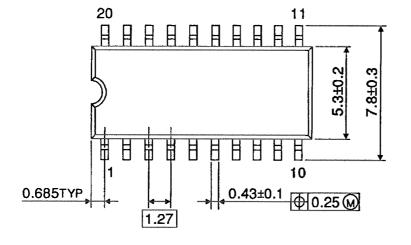


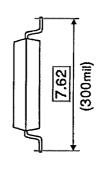
Weight: 1.48 g (typ.)

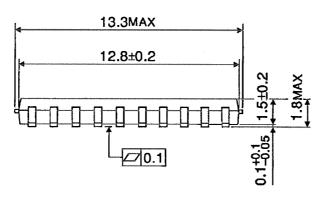
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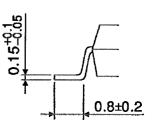
# **Package Dimensions**

SOP20-P-300-1.27 Unit: mm









Weight: 0.25 g (typ.)

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